

RURD620CC, RURD620CCS

Data Sheet January 2000 File Number 4075.2

6A, 200V Ultrafast Dual Diodes

The RURD620CC and RURD620CCS are ultrafast dual diodes with soft recovery characteristics (t_{rr} < 25ns). They have low forward voltage drop and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Formerly developmental type TA49037.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RURD620CC	TO-251AA	UR620C
RURD620CCS	TO-252AA	UR620C

NOTE: When ordering, use the entire part number. Add the suffix, 9A, to obtain the TO-252 variant in tape and reel, i.e., RURD620CCS9A.

Symbol



Features

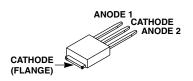
- Ultrafast with Soft Recovery
 Operating Temperature
 Reverse Voltage
 200V
- · Avalanche Energy Rated
- Planar Construction

Applications

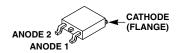
- · Switching Power Supplies
- · Power Switching Circuits
- General Purpose

Packaging

JEDEC TO-251AA



JEDEC TO-252AA



DIIDDESUCC

Absolute Maximum Ratings (Per Leg) $T_C = 25^{\circ}C$ Unless Otherwise Specified

	RURD620CCS	UNITS
Peak Repetitive Reverse Voltage	200	V
Working Peak Reverse Voltage	200	V
DC Blocking VoltageV _R	200	V
Average Rectified Forward Current	6	Α
Repetitive Peak Surge Current	12	Α
Nonrepetitive Peak Surge Current	60	Α
Maximum Power Dissipation	45	W
Avalanche Energy (See Figures 10 and 11)	10	mJ
Operating and Storage Temperature	-65 to 175	°С

RURD620CC, RURD620CCS

Electrical Specifications (Per Leg) $T_C = 25^{\circ}C$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	ТҮР	MAX	UNITS
V _F	I _F = 6A	-	-	1.0	V
	I _F = 6A, T _C = 150°C	-	-	0.83	V
I _R	V _R = 200V	-	-	100	μΑ
	$V_R = 200V, T_C = 150^{\circ}C$	-	-	500	μΑ
t _{rr}	$I_F = 1A$, $dI_F/dt = 200A/\mu s$	-	-	25	ns
	$I_F = 6A$, $dI_F/dt = 200A/\mu s$	-	-	30	ns
ta	$I_F = 6A$, $dI_F/dt = 200A/\mu s$	-	13	-	ns
t _b	$I_F = 6A$, $dI_F/dt = 200A/\mu s$	-	6.5	-	ns
Q _{RR}	$I_F = 6A$, $dI_F/dt = 200A/\mu s$	-	20	-	nC
CJ	V _R = 10V, I _F = 0A	-	30	-	pf
$R_{ heta JC}$		-	-	3.5	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

 I_R = Instantaneous reverse current.

 t_{rr} = Reverse recovery time (See Figure 9), summation of t_a + t_b .

t_a = Time to reach peak reverse current (See Figure 9).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

 Q_{RR} = Reverse recovery charge.

C_J = Junction Capacitance.

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

Typical Performance Curves

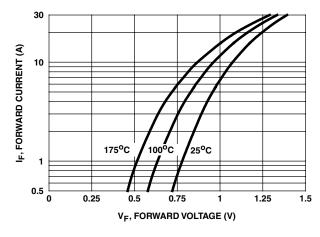


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

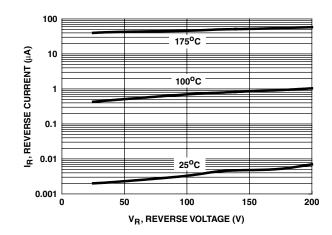


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

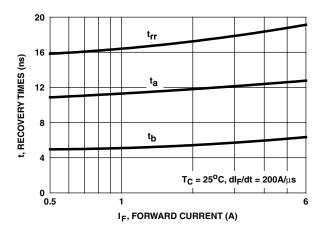


FIGURE 3. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

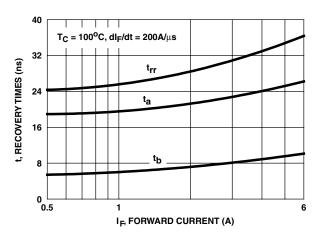


FIGURE 4. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

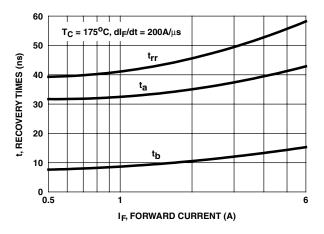


FIGURE 5. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

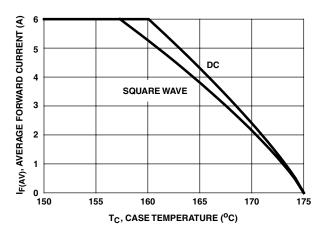


FIGURE 6. CURRENT DERATING CURVE

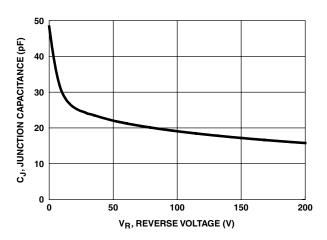


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

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RURD620CC, RURD620CCS

Test Circuits and Waveforms

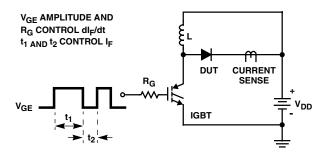


FIGURE 8. t_{rr} TEST CIRCUIT

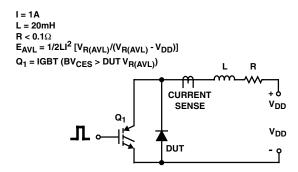


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

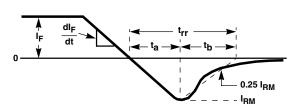


FIGURE 9. t_{rr} WAVEFORMS AND DEFINITIONS

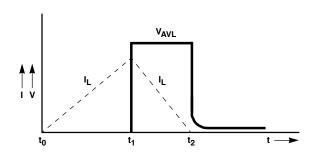


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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DOME™	ISOPLANAR™	QT Optoelectronics™	UHC TM
EcoSPARK™	LittleFET™	Quiet Series™	UltraFET™
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PRODUCT STATUS DEFINITIONS

Definition of Terms

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